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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I <sup>2</sup> C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, Motor Control PWM, QEI, POR, PWM, WDT
Number of I/O	20
Program Memory Size	12KB (4K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 6x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SOIC (0.295", 7.50mm Width)
Supplier Device Package	28-SOIC
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/dspic30f2010t-20i-so">https://www.e-xfl.com/product-detail/microchip-technology/dspic30f2010t-20i-so</a>

# dsPIC30F Flash Programming Specification

## 3.0 PROGRAMMING EXECUTIVE APPLICATION

### 3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
  - Code memory and data EEPROM
  - Configuration registers
  - Device ID
- Erase memory
  - Bulk Erase by segment
  - Code memory (by row)
  - Data EEPROM (by row)
- Program memory
  - Code memory
  - Data EEPROM
  - Configuration registers
- Query
  - Blank Device
  - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in [Section 5.0 “Device Programming”](#).

### 3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

### 3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

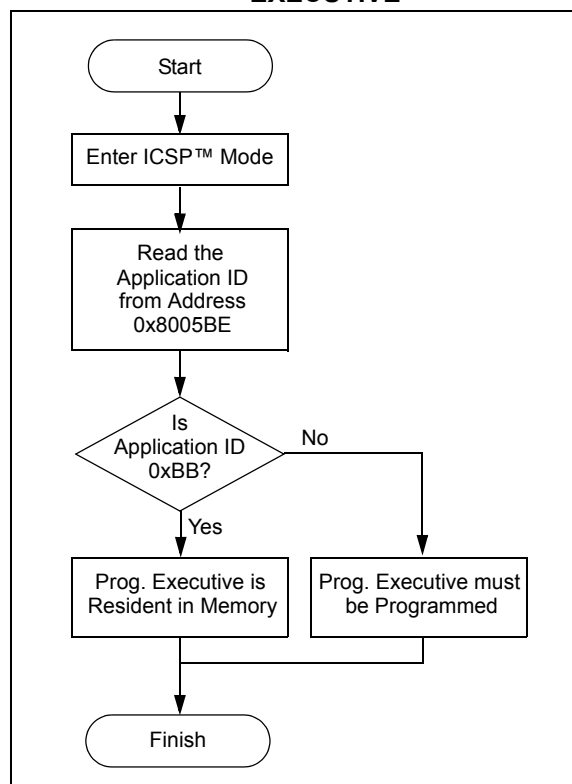
## 4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in [Figure 4-1](#).

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

[Section 11.0 “ICSP™ Mode”](#) describes the process for the ICSP programming method. [Section 11.13 “Reading the Application ID Word”](#) describes the procedure for reading the application ID word in ICSP mode.

**FIGURE 4-1: CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE**

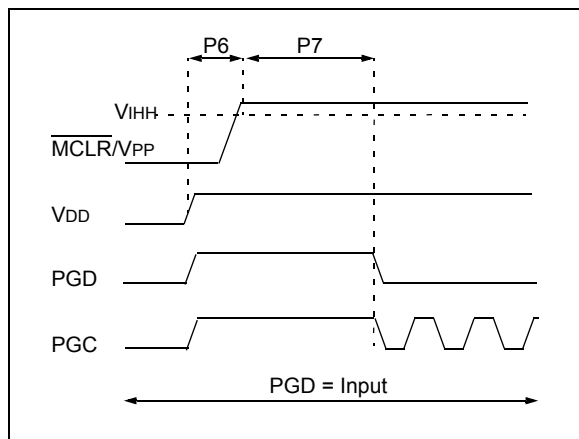


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## 5.2 Entering Enhanced ICSP Mode

The Enhanced ICSP mode is entered by holding PGC and PGD high, and then raising MCLR/VPP to VIH (high voltage), as illustrated in Figure 5-2. In this mode, the code memory, data EEPROM and Configuration bits can be efficiently programmed using the programming executive commands that are serially transferred using PGC and PGD.

**FIGURE 5-2: ENTERING ENHANCED ICSP™ MODE**



**Note 1:** The sequence that places the device into Enhanced ICSP mode places all unused I/Os in the high-impedance state.

**2:** Before entering Enhanced ICSP mode, clock switching must be disabled using ICSP, by programming the FCKSM<1:0> bits in the FOSC Configuration register to '11' or '10'.

**3:** When in Enhanced ICSP mode, the SPI output pin (SDO1) will toggle while the device is being programmed.

## 5.3 Chip Erase

Before a chip can be programmed, it must be erased. The Bulk Erase command (**ERASEB**) is used to perform this task. Executing this command with the MS command field set to 0x3 erases all code memory, data EEPROM and code-protect Configuration bits. The Chip Erase process sets all bits in these three memory regions to '1'.

Since non-code-protect Configuration bits cannot be erased, they must be manually set to '1' using multiple **PROGC** commands. One **PROGC** command must be sent for each Configuration register (see [Section 5.7 "Configuration Bits Programming"](#)).

If Advanced Security features are enabled, then individual Segment Erase operations would need to be performed, depending on which segment needs to be programmed at a given stage of system programming. The user should have the flexibility to select specific segments for programming.

**Note:** The Device ID registers cannot be erased. These registers remain intact after a Chip Erase is performed.

## 5.4 Blank Check

The term "Blank Check" means to verify that the device has been successfully erased and has no programmed memory cells. A blank or erased memory cell reads as '1'. The following memories must be blank checked:

- All implemented code memory
- All implemented data EEPROM
- All Configuration bits (for their default value)

The Device ID registers (0xFF0000:0xFF0002) can be ignored by the Blank Check since this region stores device information that cannot be erased. Additionally, all unimplemented memory space should be ignored from the Blank Check.

The **QBLANK** command is used for the Blank Check. It determines if the code memory and data EEPROM are erased by testing these memory regions. A 'BLANK' or 'NOT BLANK' response is returned. The **READD** command is used to read the Configuration registers. If it is determined that the device is not blank, it must be erased (see [Section 5.3 "Chip Erase"](#)) before attempting to program the chip.

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## 5.5 Code Memory Programming

### 5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see Table 5-2).

**TABLE 5-2: DEVICE CODE MEMORY SIZE**

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

### 5.5.2 PROGRAMMING METHODOLOGY

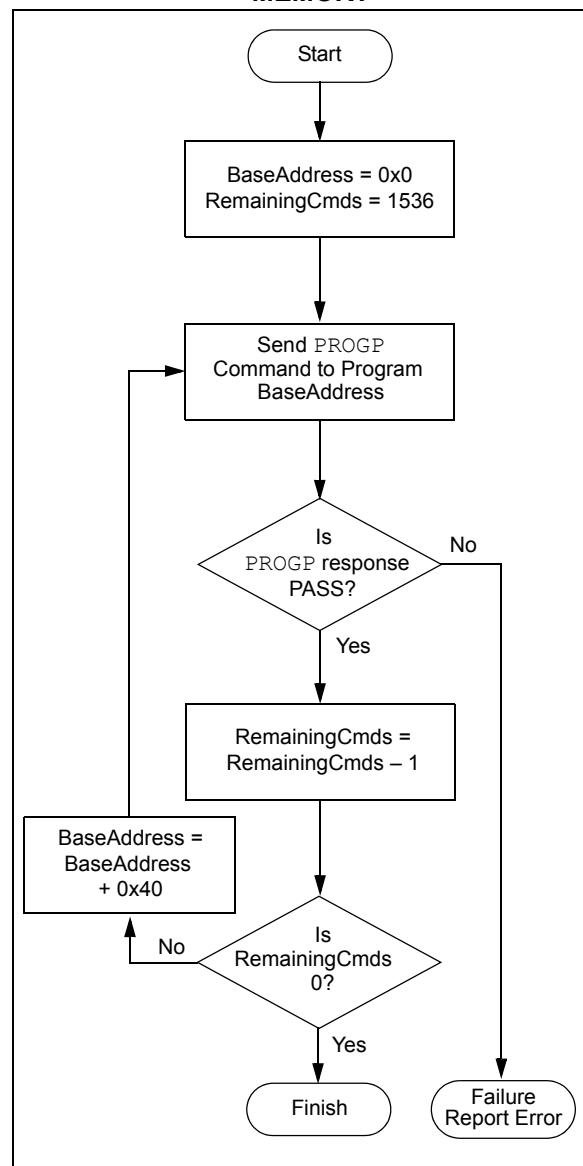
Code memory is programmed with the `PROGP` command. `PROGP` programs one row of code memory to the memory address specified in the command. The number of `PROGP` commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in Figure 5-3. In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a `PROGP` command. Each `PROGP` command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more `PROGP` commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second `PROGP` command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

**FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY**



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## 5.6.3 PROGRAMMING VERIFICATION

Once the data EEPROM is programmed, the contents of memory can be verified to ensure that the programming was successful. Verification requires the data EEPROM to be read back and compared against the copy held in the programmer's buffer. The `READD` command reads back the programmed data EEPROM.

Alternatively, the programmer can perform the verification once the entire device is programmed using a checksum computation, as described in [Section 6.8 "Checksum Computation"](#).

**Note:** `TBLRDL` instructions executed within a `REPEAT` loop must not be used to read from Data EEPROM. Instead, it is recommended to use PSV access.

## 5.7 Configuration Bits Programming

### 5.7.1 OVERVIEW

The dsPIC30F has Configuration bits stored in seven 16-bit registers. These bits can be set or cleared to select various device configurations. There are two types of Configuration bits: system-operation bits and code-protect bits. The system-operation bits determine the power-on settings for system-level components such as the oscillator and Watchdog Timer. The code-protect bits prevent program memory from being read and written.

The FOSC Configuration register has three different register descriptions, based on the device. The FOSC Configuration register description for the dsPIC30F2010 and dsPIC30F6010/6011/6012/6013/6014 devices are shown in [Table 5-4](#).

**Note:** If user software performs an erase operation on the configuration fuse, it must be followed by a write operation to this fuse with the desired value, even if the desired value is the same as the state of the erased fuse.

The FOSC Configuration register description for the dsPIC30F4011/4012 and dsPIC30F5011/5013 devices is shown in [Table 5-5](#).

The FOSC Configuration register description for all remaining devices (dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013, dsPIC30F3014/4013, dsPIC30F5015 and dsPIC30F6011A/6012A/6013A/6014A) is shown in [Table 5-6](#). Always use the correct register descriptions for your target processor.

The `FWDT`, `FBORPOR`, `FBS`, `FSS`, `FGS` and `FICD` Configuration registers are not device-dependent. The register descriptions for these Configuration registers are shown in [Table 5-7](#).

The Device Configuration register maps are shown in [Table 5-8](#) through [Table 5-11](#).

**TABLE 5-4: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2010 AND dsPIC30F6010/6011/6012/6013/6014**

Bit Field	Register	Description
FCKSM<1:0>	FOSC	<b>Clock Switching Mode</b> 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<1:0>	FOSC	<b>Oscillator Source Selection on POR</b> 11 = Primary Oscillator 10 = Internal Low-Power RC Oscillator 01 = Internal Fast RC Oscillator 00 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<3:0>	FOSC	<b>Primary Oscillator Mode</b> 1111 = ECIO w/PLL 16X – External Clock mode with 16X PLL. OSC2 pin is I/O 1110 = ECIO w/PLL 8X – External Clock mode with 8X PLL. OSC2 pin is I/O 1101 = ECIO w/PLL 4X – External Clock mode with 4X PLL. OSC2 pin is I/O 1100 = ECIO – External Clock mode. OSC2 pin is I/O 1011 = EC – External Clock mode. OSC2 pin is system clock output (Fosc/4) 1010 = Reserved (do not use) 1001 = ERC – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is I/O 0111 = XT w/PLL 16X – XT Crystal Oscillator mode with 16X PLL 0110 = XT w/PLL 8X – XT Crystal Oscillator mode with 8X PLL 0101 = XT w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0100 = XT – XT Crystal Oscillator mode (4 MHz-10 MHz crystal) 001x = HS – HS Crystal Oscillator mode (10 MHz-25 MHz crystal) 000x = XTL – XTL Crystal Oscillator mode (200 kHz-4 MHz crystal)

**TABLE 5-8: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2010, dsPIC30F4011/4012 AND dsPIC30F6010/ 6011/6012/6013/ 6014)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN <sup>(1)</sup>	HPOL <sup>(1)</sup>	LPOL <sup>(1)</sup>	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved <sup>(2)</sup>		—	—	—	Reserved <sup>(2)</sup>	—	—	—	—	Reserved <sup>(2)</sup>			
0xF80008	FSS	—	—	Reserved <sup>(2)</sup>		—	—	Reserved <sup>(2)</sup>		—	—	—	—	Reserved <sup>(2)</sup>			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved <sup>(2)</sup>	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note 1:** On the 6011, 6012, 6013 and 6014, these bits are reserved (read as '1' and must be programmed as '1').

**Note 2:** Reserved bits read as '1' and must be programmed as '1'.

**TABLE 5-9: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F5011/5013)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	Reserved <sup>(1)</sup>			BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note 1:** Reserved bits read as '1' and must be programmed as '1'.

# dsPIC30F Flash Programming Specification

## 5.7.2 PROGRAMMING METHODOLOGY

System operation Configuration bits are inherently different than all other memory cells. Unlike code memory, data EEPROM and code-protect Configuration bits, the system operation bits cannot be erased. If the chip is erased with the `ERASEB` command, the system-operation bits retain their previous value. Consequently, you should make no assumption about the value of the system operation bits. They should always be programmed to their desired setting.

Configuration bits are programmed as a single word at a time using the `PROGC` command. The `PROGC` command specifies the configuration data and Configuration register address. When Configuration bits are programmed, any unimplemented bits must be programmed with a '0', and any reserved bits must be programmed with a '1'.

Four `PROGC` commands are required to program all the Configuration bits. Figure 5-5 illustrates the flowchart of Configuration bit programming.

**Note:** If the General Code Segment Code Protect (GCP) bit is programmed to '0', code memory is code-protected and cannot be read. Code memory must be verified before enabling read protection. See Section 5.7.4 "Code-Protect Configuration Bits" for more information about code-protect Configuration bits.

## 5.7.3 PROGRAMMING VERIFICATION

Once the Configuration bits are programmed, the contents of memory should be verified to ensure that the programming was successful. Verification requires the Configuration bits to be read back and compared against the copy held in the programmer's buffer. The `READD` command reads back the programmed Configuration bits and verifies whether the programming was successful.

Any unimplemented Configuration bits are read-only and read as '0'.

## 5.7.4 CODE-PROTECT CONFIGURATION BITS

The FBS, FSS and FGS Configuration registers are special Configuration registers that control the size and level of code protection for the Boot Segment, Secure Segment and General Segment, respectively. For each segment, two main forms of code protection are provided. One form prevents code memory from being written (write protection), while the other prevents code memory from being read (read protection).

The BWRP, SWRP and GWRP bits control write protection; and BSS<2:0>, SSS<2:0> and GSS<1:0> bits control read protection. The Chip Erase `ERASEB` command sets all the code protection bits to '1', which allows the device to be programmed.

When write protection is enabled, any programming operation to code memory will fail. When read protection is enabled, any read from code memory will cause a '0x0' to be read, regardless of the actual contents of code memory. Since the programming executive always verifies what it programs, attempting to program code memory with read protection enabled will also result in failure.

It is imperative that all code protection bits are '1' while the device is being programmed and verified. Only after the device is programmed and verified should any of the above bits be programmed to '0' (see Section 5.7 "Configuration Bits Programming").

In addition to code memory protection, parts of data EEPROM and/or data RAM can be configured to be accessible only by code resident in the Boot Segment and/or Secure Segment. The sizes of these "reserved" sections are user-configurable, using the EBS, RBS<1:0>, ESS<1:0> and RSS<1:0> bits.

**Note 1:** All bits in the FBS, FSS and FGS Configuration registers can only be programmed to a value of '0'. `ERASEB` is the only way to reprogram code-protect bits from ON ('0') to OFF ('1').

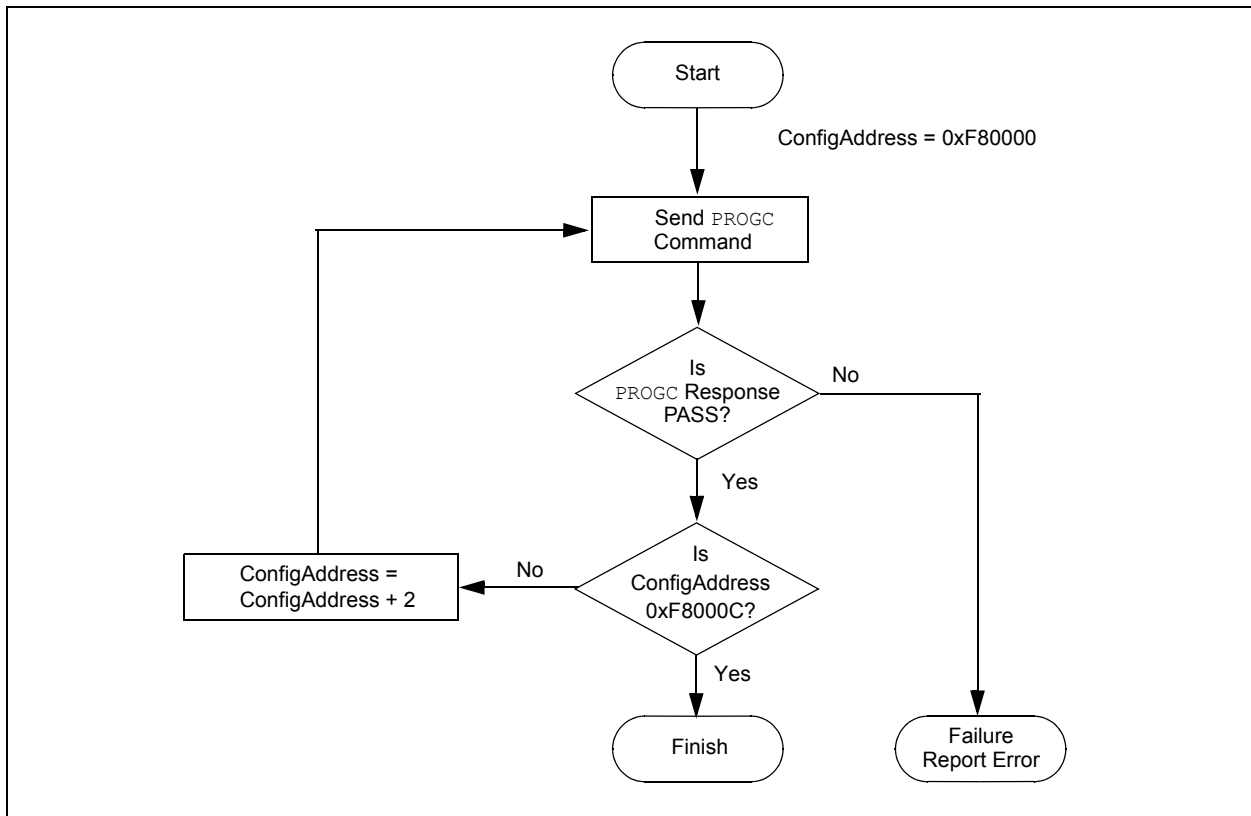
**2:** If any of the code-protect bits in FBS, FSS, or FGS are clear, the entire device must be erased before it can be reprogrammed.

# dsPIC30F Flash Programming Specification

## 5.8 Exiting Enhanced ICSP Mode

The Enhanced ICSP mode is exited by removing power from the device or bringing MCLR to V<sub>IL</sub>. When normal user mode is next entered, the program that was stored using Enhanced ICSP will execute.

**FIGURE 5-5: CONFIGURATION BIT PROGRAMMING FLOW**





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TABLE 8-1: PROGRAMMING EXECUTIVE COMMAND SET

Opcode	Mnemonic	Length (16-bit words)	Time Out	Description
0x0	SCHECK	1	1 ms	Sanity check.
0x1	READD	4	1 ms/row	Read N 16-bit words of data EEPROM, Configuration registers or device ID starting from specified address.
0x2	READP	4	1 ms/row	Read N 24-bit instruction words of code memory starting from specified address.
0x3	Reserved	N/A	N/A	This command is reserved. It will return a NACK.
0x4	PROGD <sup>(2)</sup>	19	5 ms	Program one row of data EEPROM at the specified address, then verify.
0x5	PROGP <sup>(1)</sup>	51	5 ms	Program one row of code memory at the specified address, then verify.
0x6	PROGC	4	5 ms	Write byte or 16-bit word to specified Configuration register.
0x7	ERASEB	2	5 ms	Bulk Erase (entire code memory or data EEPROM), or erase by segment.
0x8	ERASED <sup>(2)</sup>	3	5 ms/row	Erase rows of data EEPROM from specified address.
0x9	ERASEP <sup>(1)</sup>	3	5 ms/row	Erase rows of code memory from specified address.
0xA	QBLANK	3	300 ms	Query if the code memory and data EEPROM are blank.
0xB	QVER	1	1 ms	Query the programming executive software version.

**Note 1:** One row of code memory consists of (32) 24-bit words. Refer to [Table 5-2](#) for device-specific information.

**Note 2:** One row of data EEPROM consists of (16) 16-bit words. Refer to [Table 5-3](#) for device-specific information.

# dsPIC30F Flash Programming Specification

## 8.5.3 READP COMMAND

15	12	11	8	7	0
Opcode		Length			
N					
Reserved			Addr_MSB		
Addr_LS					

Field	Description
Opcode	0x2
Length	0x4
N	Number of 24-bit instructions to read (max of 32768)
Reserved	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The **READP** command instructs the programming executive to read N 24-bit words of code memory starting from the 24-bit address specified by Addr\_MSB and Addr\_LS. This command can only be used to read 24-bit data. All data returned in response to this command uses the packed data format described in [Section 8.3 “Packed Data Format”](#).

### Expected Response (2 + 3 \* N/2 words for N even):

0x1200

2 + 3 \* N/2

Least significant program memory word 1

...

Least significant data word N

### Expected Response (4 + 3 \* (N – 1)/2 words for N odd):

0x1200

4 + 3 \* (N – 1)/2

Least significant program memory word 1

...

MSB of program memory word N (zero padded)

**Note:** Reading unimplemented memory will cause the programming executive to reset.

## 8.5.4 PROGD COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_16					

Field	Description
Opcode	0x4
Length	0x13
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data words 3 through 15
D_16	16-bit data word 16

The **PROGD** command instructs the programming executive to program one row of data EEPROM. The data to be programmed is specified by the 16 data words (D\_1, D\_2,..., D\_16) and is programmed to the destination address specified by Addr\_MSB and Addr\_LSB. The destination address should be a multiple of 0x20.

Once the row of data EEPROM has been programmed, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1400

0x0002

**Note:** Refer to [Table 5-3](#) for data EEPROM size information.

# dsPIC30F Flash Programming Specification

## 9.2.3 QE\_Code FIELD

The QE\_Code is a byte in the first word of the response. This byte is used to return data for query commands, and error codes for all other commands.

When the programming executive processes one of the two query commands (`QBLANK` or `QVER`), the returned opcode is always PASS and the QE\_Code holds the query response data. The format of the QE\_Code for both queries is shown in [Table 9-3](#).

**TABLE 9-3: QE\_Code FOR QUERIES**

Query	QE_Code
QBLANK	0x0F = Code memory and data EEPROM are NOT blank 0xF0 = Code memory and data EEPROM are blank
QVER	0xMN, where programming executive software version = M.N (i.e., 0x32 means software version 3.2)

When the programming executive processes any command other than a Query, the QE\_Code represents an error code. Supported error codes are shown in [Table 9-4](#). If a command is successfully processed, the returned QE\_Code is set to 0x0, which indicates that there was no error in the command processing. If the verify of the programming for the `PROGD`, `PROGP` or `PROGC` command fails, the QE\_Code is set to 0x1. For all other programming executive errors, the QE\_Code is 0x2.

**TABLE 9-4: QE\_Code FOR NON-QUERY COMMANDS**

QE_Code	Description
0x0	No error
0x1	Verify failed
0x2	Other error

## 9.2.4 RESPONSE LENGTH

The response length indicates the length of the programming executive's response in 16-bit words. This field includes the 2 words of the response header.

With the exception of the response for the `READD` and `READP` commands, the length of each response is only 2 words.

The response to the `READD` command is  $N + 2$  words, where  $N$  is the number of words specified in the `READD` command.

The response to the `READP` command uses the packed instruction word format described in [Section 8.3 "Packed Data Format"](#). When reading an odd number of program memory words ( $N$  odd), the response to the `READP` command is  $(3 \cdot (N + 1)/2 + 2)$  words. When reading an even number of program memory words ( $N$  even), the response to the `READP` command is  $(3 \cdot N/2 + 2)$  words.

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## 10.0 DEVICE ID

The device ID region is 2 x 16 bits and can be read using the `READD` command. This region of memory is read-only and can also be read when code protection is enabled.

Table 10-1 shows the device ID for each device, Table 10-2 shows the device ID registers and Table 10-3 describes the bit field of each register.

**TABLE 10-1: DEVICE IDS**

Device	DEVID	Silicon Revision							
		A0	A1	A2	A3	A4	B0	B1	B2
dsPIC30F2010	0x0040	0x1000	0x1001	0x1002	0x1003	0x1004	—	—	—
dsPIC30F2011	0x0240	—	0x1001	—	—	—	—	—	—
dsPIC30F2012	0x0241	—	0x1001	—	—	—	—	—	—
dsPIC30F3010	0x01C0	0x1000	0x1001	0x1002	—	—	—	—	—
dsPIC30F3011	0x01C1	0x1000	0x1001	0x1002	—	—	—	—	—
dsPIC30F3012	0x00C1	—	—	—	—	—	0x1040	0x1041	—
dsPIC30F3013	0x00C3	—	—	—	—	—	0x1040	0x1041	—
dsPIC30F3014	0x0160	—	0x1001	0x1002	—	—	—	—	—
dsPIC30F4011	0x0101	—	0x1001	0x1002	0x1003	0x1003	—	—	—
dsPIC30F4012	0x0100	—	0x1001	0x1002	0x1003	0x1003	—	—	—
dsPIC30F4013	0x0141	—	0x1001	0x1002	—	—	—	—	—
dsPIC30F5011	0x0080	—	0x1001	0x1002	0x1003	0x1003	—	—	—
dsPIC30F5013	0x0081	—	0x1001	0x1002	0x1003	0x1003	—	—	—
dsPIC30F5015	0x0200	0x1000	—	—	—	—	—	—	—
dsPIC30F5016	0x0201	0x1000	—	—	—	—	—	—	—
dsPIC30F6010	0x0188	—	—	—	—	—	—	0x1040	0x1042
dsPIC30F6010A	0x0281	—	—	0x1002	0x1003	0x1004	—	—	—
dsPIC30F6011	0x0192	—	—	—	0x1003	—	—	0x1040	0x1042
dsPIC30F6011A	0x02C0	—	—	0x1002	—	—	0x1040	0x1041	—
dsPIC30F6012	0x0193	—	—	—	0x1003	—	—	0x1040	0x1042
dsPIC30F6012A	0x02C2	—	—	0x1002	—	—	0x1040	0x1041	—
dsPIC30F6013	0x0197	—	—	—	0x1003	—	—	0x1040	0x1042
dsPIC30F6013A	0x02C1	—	—	0x1002	—	—	0x1040	0x1041	—
dsPIC30F6014	0x0198	—	—	—	0x1003	—	—	0x1040	0x1042
dsPIC30F6014A	0x02C3	—	—	0x1002	—	—	0x1040	0x1041	—
dsPIC30F6015	0x0280	—	—	0x1002	0x1003	0x1004	—	—	—

**TABLE 10-2: dsPIC30F DEVICE ID REGISTERS**

Address	Name	Bit															
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
0xFF0000	DEVID	DEVID<15:0>															
0xFF0002	DEVREV	PROC<3:0>				REV<5:0>						DOT<5:0>					

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## 11.0 ICSP™ MODE

### 11.1 ICSP Mode

ICSP mode is a special programming protocol that allows you to read and write to the dsPIC30F programming executive. The ICSP mode is the second (and slower) method used to program the device. This mode also has the ability to read the contents of executive memory to determine whether the programming executive is present. This capability is accomplished by applying control codes and instructions serially to the device using pins PGC and PGD.

In ICSP mode, the system clock is taken from the PGC pin, regardless of the device's oscillator Configuration bits. All instructions are first shifted serially into an internal buffer, then loaded into the Instruction register and executed. No program fetching occurs from internal memory. Instructions are fed in 24 bits at a time. PGD is used to shift data in and PGC is used as both the serial shift clock and the CPU execution clock.

Data is transmitted on the rising edge and latched on the falling edge of PGC. For all data transmissions, the Least Significant bit (LSb) is transmitted first.

**Note 1:** During ICSP operation, the operating frequency of PGC must not exceed 5 MHz.

**2:** Because ICSP is slower, it is recommended that only Enhanced ICSP (E-ICSP) mode be used for device programming, as described in [Section 5.1 "Overview of the Programming Process"](#).

### 11.2 ICSP Operation

Upon entry into ICSP mode, the CPU is idle. Execution of the CPU is governed by an internal state machine. A 4-bit control code is clocked in using PGC and PGD, and this control code is used to command the CPU (see [Table 11-1](#)).

The SIX control code is used to send instructions to the CPU for execution, while the REGOUT control code is used to read data out of the device via the VISI register. The operation details of ICSP mode are provided in [Section 11.2.1 "SIX Serial Instruction Execution"](#) and [Section 11.2.2 "REGOUT Serial Instruction Execution"](#).

**TABLE 11-1: CPU CONTROL CODES IN ICSP™ MODE**

4-bit Control Code	Mnemonic	Description
0000b	SIX	Shift in 24-bit instruction and execute.
0001b	REGOUT	Shift out the VISI register.
0010b-1111b	N/A	Reserved.

#### 11.2.1 SIX SERIAL INSTRUCTION EXECUTION

The SIX control code allows execution of dsPIC30F assembly instructions. When the SIX code is received, the CPU is suspended for 24 clock cycles as the instruction is then clocked into the internal buffer. Once the instruction is shifted in, the state machine allows it to be executed over the next four clock cycles. While the received instruction is executed, the state machine simultaneously shifts in the next 4-bit command (see [Figure 11-2](#)).

**Note 1:** Coming out of the ICSP entry sequence, the first 4-bit control code is always forced to SIX and a forced NOP instruction is executed by the CPU. Five additional PGC clocks are needed on start-up, thereby resulting in a 9-bit SIX command instead of the normal 4-bit SIX command. After the forced SIX is clocked in, ICSP operation resumes as normal (the next 24 clock cycles load the first instruction word to the CPU). See [Figure 11-1](#) for details.

**2:** TBLRDH, TBLRDL, TBLWTH and TBLWTL instructions must be followed by a NOP instruction.

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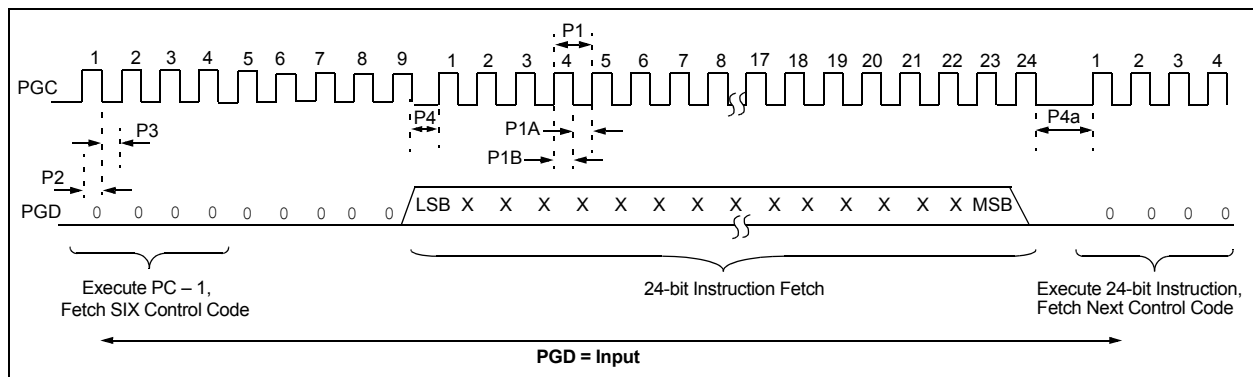
## 11.2.2 REGOUT SERIAL INSTRUCTION EXECUTION

The REGOUT control code allows for data to be extracted from the device in ICSP mode. It is used to clock the contents of the VISI register out of the device over the PGD pin. Once the REGOUT control code is received, eight clock cycles are required to process the command. During this time, the CPU is held idle. After these eight cycles, an additional 16 cycles are required to clock the data out (see Figure 11-3).

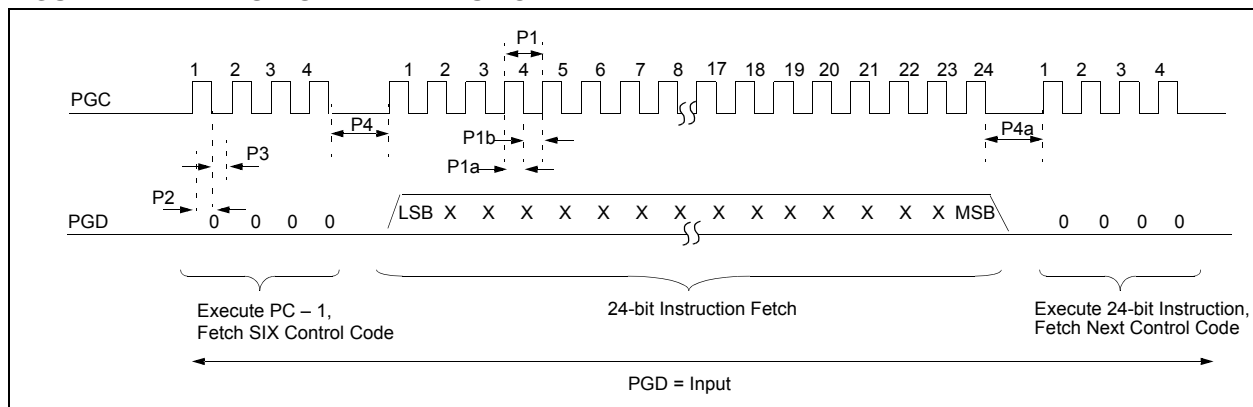
The REGOUT instruction is unique because the PGD pin is an input when the control code is transmitted to the device. However, once the control code is processed, the PGD pin becomes an output as the VISI register is shifted out. After the contents of the VISI are shifted out, PGD becomes an input again as the state machine holds the CPU idle until the next 4-bit control code is shifted in.

**Note:** Once the contents of VISI are shifted out, the dsPIC® DSC device maintains PGD as an output until the first rising edge of the next clock is received.

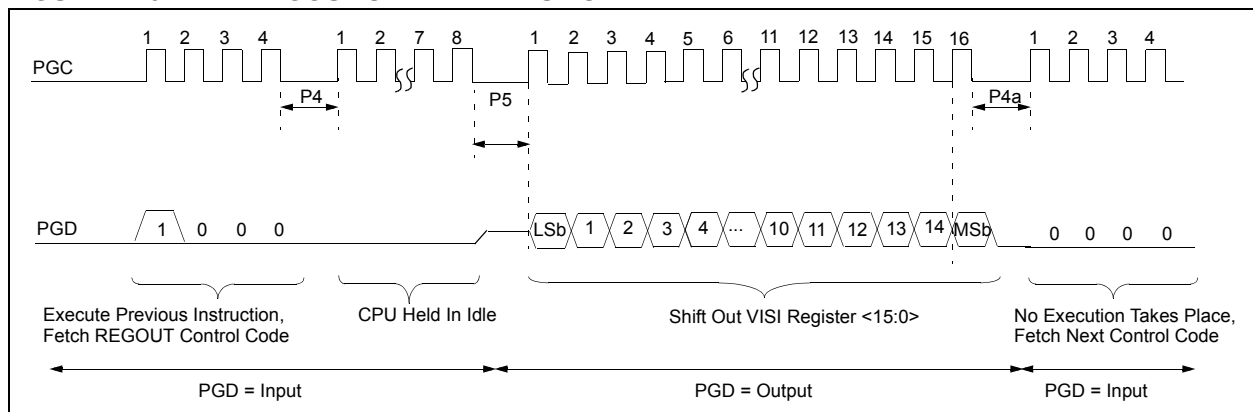
**FIGURE 11-1: PROGRAM ENTRY AFTER RESET**



**FIGURE 11-2: SIX SERIAL EXECUTION**



**FIGURE 11-3: REGOUT SERIAL EXECUTION**



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Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

**Note:** Program memory must be erased before writing any data to program memory.

**TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Set NVMCON to program the FBS Configuration register.<sup>(1)</sup></b>		
0000	24008A	MOV #0x4008, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.<sup>(1)</sup></b>		
0000	200F80	MOV #0xF8, W0
0000	880190	MOV W0, TBLPAG
0000	200067	MOV #0x6, W7
<b>Step 4: Load the Configuration Register data to W6.<sup>(1)</sup></b>		
0000	EB0300	CLR W6
0000	000000	NOP
<b>Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.<sup>(1)</sup></b>		
0000	BB1B86	TBLWTL W6, [W7++]
<b>Step 6: Unlock the NVMCON for programming the Configuration register.<sup>(1)</sup></b>		
0000	200558	MOV #0x55, W8
0000	200AA9	MOV #0xAA, W9
0000	883B38	MOV W8, NVMKEY
0000	883B39	MOV W9, NVMKEY
<b>Step 7: Initiate the programming cycle.<sup>(1)</sup></b>		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 2 ms
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.<sup>(1)</sup></b>		
<b>Step 9: Set the NVMCON to erase all Program Memory.</b>		
00000	2407FA	MOV #0x407F, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 10: Unlock the NVMCON for programming.</b>		

**Note 1:** Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

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**TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 6:</b> Write the Configuration register data to the write latch and increment the write pointer.		
0000	BB1B96	TBLWTL W6, [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 7:</b> Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8:</b> Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10:</b> Repeat steps 3-9 until all 7 Configuration registers are cleared.		



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## 11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

**TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.</b>		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
<b>Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.</b>		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 4: Output W0:W5 using the VISI register and REGOUT command.</b>		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 until all desired data memory is read.</b>		

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## 11.13 Reading the Application ID Word

The application ID word is stored at address 0x8005BE in executive code memory. To read this memory location, you must use the SIX control code to move this program memory location to the VISI register. The REGOUT control code must then be used to clock the contents of the VISI register out of the device. The corresponding control and instruction codes that must be serially transmitted to the device to perform this operation are shown in [Table 11-13](#).

Once the programmer has clocked-out the application ID word, it must be inspected. If the application ID has the value 0xBB, the programming executive is resident in memory and the device can be programmed using the mechanism described in [Section 5.0 “Device Programming”](#). However, if the application ID has any other value, the programming executive is not resident in memory. It must be loaded to memory before the device can be programmed. The procedure for loading the programming executive to the memory is described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

## 11.14 Exiting ICSP Mode

After confirming that the programming executive is resident in memory, or loading the programming executive, ICSP mode is exited by removing power to the device or bringing MCLR to V<sub>IL</sub>. Programming can then take place by following the procedure outlined in [Section 5.0 “Device Programming”](#).

**TABLE 11-13: SERIAL INSTRUCTION EXECUTION FOR READING THE APPLICATION ID WORD**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W0) for TBLRD instruction.</b>		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	205BE0	MOV #0x5BE, W0
0000	207841	MOV VISI, W1
0000	000000	NOP
0000	BA0890	TBLRDL [W0], [W1]
0000	000000	NOP
0000	000000	NOP
<b>Step 3: Output the VISI register using the REGOUT command.</b>		
0001	<VISI>	Clock out contents of the VISI register
0000	000000	NOP

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**TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 8:</b> Set the read pointer (W6) and load the (next four write) latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Repeat Steps 7-8 eight times to load the write latches for the 32 instructions.		
<b>Step 10:</b> Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 11:</b> Initiate the programming cycle.		
0000	A8E761	BSET NVMCON, #15
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #15
0000	000000	NOP
0000	000000	NOP
<b>Step 12:</b> Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 13:</b> Repeat Steps 7-12 until all 23 rows of executive memory are programmed.		

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## 13.0 AC/DC CHARACTERISTICS AND TIMING REQUIREMENTS

TABLE 13-1: AC/DC CHARACTERISTICS

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
D110	VIHH	High Programming Voltage on $\overline{\text{MCLR}}/\text{VPP}$	9.00	13.25	V	—
D112	I <sub>PP</sub>	Programming Current on $\overline{\text{MCLR}}/\text{VPP}$	—	300	μA	—
D113	I <sub>DDP</sub>	Supply Current during programming	—	30	mA	Row Erase Program memory
			—	30	mA	Row Erase Data EEPROM
			—	30	mA	Bulk Erase
D001	V <sub>DD</sub>	Supply voltage	2.5	5.5	V	—
D002	V <sub>DD</sub> BULK	Supply voltage for Bulk Erase programming	4.5	5.5	V	—
D031	V <sub>IL</sub>	Input Low Voltage	V <sub>SS</sub>	0.2 V <sub>SS</sub>	V	—
D041	V <sub>IH</sub>	Input High Voltage	0.8 V <sub>DD</sub>	V <sub>DD</sub>	V	—
D080	V <sub>OL</sub>	Output Low Voltage	—	0.6	V	I <sub>OL</sub> = 8.5 mA
D090	V <sub>OH</sub>	Output High Voltage	V <sub>DD</sub> - 0.7	—	V	I <sub>OH</sub> = -3.0 mA
D012	C <sub>IO</sub>	Capacitive Loading on I/O Pin (PGD)	—	50	pF	To meet AC specifications
P1	T <sub>SCLK</sub>	Serial Clock (PGC) period	50	—	ns	ICSP™ mode
			1	—	μs	Enhanced ICSP mode
P1a	T <sub>SCLKL</sub>	Serial Clock (PGC) low time	20	—	ns	ICSP mode
			400	—	ns	Enhanced ICSP mode
P1b	T <sub>SCLKH</sub>	Serial Clock (PGC) high time	20	—	ns	ICSP mode
			400	—	ns	Enhanced ICSP mode
P2	T <sub>SET1</sub>	Input Data Setup Timer to PGC ↓	15	—	ns	—
P3	T <sub>HLD1</sub>	Input Data Hold Time from PGC ↓	15	—	ns	—
P4	T <sub>DLY1</sub>	Delay between 4-bit command and command operand	20	—	ns	—
P4a	T <sub>DLY1a</sub>	Delay between 4-bit command operand and next 4-bit command	20	—	ns	—
P5	T <sub>DLY2</sub>	Delay between last PGC ↓ of command to first PGC ↑ of VISI output	20	—	ns	—
P6	T <sub>SET2</sub>	V <sub>DD</sub> ↑ setup time to $\overline{\text{MCLR}}/\text{VPP}$	100	—	ns	—
P7	T <sub>HLD2</sub>	Input data hold time from $\overline{\text{MCLR}}/\text{VPP}$ ↑	2	—	μs	ICSP mode
			5	—	ms	Enhanced ICSP mode
P8	T <sub>DLY3</sub>	Delay between last PGC ↓ of command word to PGD driven ↑ by programming executive	20	—	μs	—
P9a	T <sub>DLY4</sub>	Programming Executive Command processing time	10	—	μs	—

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NOTES: